

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("5753535").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/02/02 13:53
L2	2	("20030197199").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/02/02 13:53
L3	2	("4883774").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/02/02 13:54
L4	2	("6117566").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/02/02 13:54
L5	2	("6194777").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/02/02 13:55
L6	2	("6294100").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/02/02 13:55
L7	2	("6498099").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/02/02 13:55
L8	2	("20010008305").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/02/02 13:56
L9	1	("0335608").PN.	USOCR; EPO; DERWENT	OR	OFF	2010/02/02 13:57
L10	0	("0335608").PN.	EPO; DERWENT	OR	OFF	2010/02/02 13:57
L11	0	("0335608").PN.	EPO; DERWENT	OR	OFF	2010/02/02 13:57
L12	0	(57/099763).APP.	JPO; DERWENT	OR	OFF	2010/02/02 14:02

L13	0	("570099763").PN.	JPO; DERWENT	OR	OFF	2010/02/02 14:02
S36	2	("4883774").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/01/19 09:38
S37	2	("6117566").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/01/19 09:39
S38	2	("6194777").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/01/19 09:39
S39	2	("6294100").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/01/19 09:40
S40	2	("6498099").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/01/19 09:41
S41	2	("20010008305").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/01/19 09:41
S42	2	("20020048825").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2010/01/19 09:42
S43	0	("0335608").PN.	EPO	OR	OFF	2010/01/19 09:43

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	(process produc\$4 lead \$1frame configur\$4 fit \$6 semiconductor chip encapsulat\$4 plastic compound interlayer attack\$5 etchant individual layer surface matrix island remain\$4 uniform height void extend\$4).clm.	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:52

S2	1	(process product\$4 lead\$1frame configur\$4 fit\$6 semiconductor chip encapsulat\$4 plastic compound interlayer attack\$5 etchant individual layer surface matrix island remain\$4 uniform height void extend\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:53
S3	1	(lead\$1frame configur\$4 semiconductor chip encapsulat\$4 plastic compound interlayer attack\$5 etchant individual layer surface matrix island remain\$4 uniform height void extend\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:53
S5	1	(lead\$1frame semiconductor encapsulat\$4 plastic compound interlayer attack\$5 etchant individual layer surface matrix island remain\$4 uniform height void extend\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:54
S6	1	(lead\$1frame semiconductor encapsulat\$4 plastic compound interlayer etchant individual layer surface matrix island remain\$4 uniform height void extend\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:54
S7	1	(lead\$1frame semiconductor encapsulat\$4 plastic compound interlayer etchant individual layer surface matrix island uniform height void extend\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:54
S8	1	(lead\$1frame semiconductor encapsulat\$4 plastic interlayer etchant individual layer surface matrix island uniform height void extend\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:54

S9	4	(lead\$1frame semiconductor encapsulat\$4 plastic interlayer etchant individual layer surface matrix island uniform height void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:54
S10	4	(lead\$1frame semiconductor encapsulat\$4 plastic interlayer etchant layer matrix island uniform height void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:57
S11	4	(lead\$1frame semiconductor encapsulat\$4 plastic interlayer etchant matrix island uniform height void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:57
S12	4	(lead\$1frame semiconductor encapsulat\$4 interlayer etchant matrix island uniform height void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:57
S13	4	(lead\$1frame semiconductor encapsulat\$4 interlayer etchant island uniform height void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:57
S14	4	(lead\$1frame encapsulat\$4 interlayer etchant island uniform height void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:57
S15	4	(lead\$1frame encapsulat\$4 interlayer etchant island uniform void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:58
S16	4	(lead\$1frame encapsulat\$4 etchant island uniform void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:58
S17	4	(lead\$1frame encapsulat\$4 etchant island void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:58
S18	338	(lead\$1frame encapsulat\$4 etchant)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:58
S19	26	(lead\$1frame encapsulat\$4 etchant island)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:59

S20	309	S18 "257".clas.	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:59
S21	154	S18 "438".clas.	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 12:59
S22	1	(lead\$1frame encapsulat \$4 etchant island).clm.	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:00
S23	9	(lead\$1frame encapsulat \$4 etchant).clm.	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:00
S24	61	(lead\$1frame encapsulat \$4 etchant void)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:01
S25	1	(lead\$1frame encapsulat \$4 etchant void).clm.	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:01
S26	51	S24 "257".clas.	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:02
S27	24	S24 "438".clas.	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:03
S28	1	(produc\$4 semiconductor leadframe base body interlayer attack\$6 etchant layers surface matrix island uniform height void chip plastic compound encapsulating hous\$4). clm.	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:08
S29	4	(semiconductor leadframe interlayer attack\$6 etchant layers surface matrix island uniform height void chip plastic compound encapsulating hous\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:09
S30	4	(semiconductor leadframe interlayer attack\$6 etchant layers surface matrix island void chip plastic compound encapsulating hous\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:09

S31	4	(semiconductor leadframe interlayer etchant layers surface matrix island void chip plastic encapsulat\$4 hous\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:09
S32	4	(semiconductor leadframe interlayer etchant layers surface matrix island void chip plastic encapsulat\$4 hous\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:09
S33	4	(leadframe interlayer etchant layers matrix island void chip plastic encapsulat\$4 hous\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:10
S34	4	(leadframe interlayer etchant island void chip plastic encapsulat\$4 hous\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:10
S35	4	(leadframe interlayer etchant island void encapsulat\$4 hous\$4)	US-PGPUB; USPAT; UPAD	AND	ON	2009/10/20 13:10

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